

V₂O₅ Thin Films Deposited by RF Magnetron Sputtering: The Influence of Oxygen Content in Physical Properties

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Abstract: Vanadium Oxide thin films were deposited by RF Magnetron sputtering using a V₂O₅ target on glass and on FTO/Glass substrates without O₂ and with a O₂ atmosphere in the deposition chamber respectively. The effects of O₂ on compositional, structural, electrical and optical properties has been studied using, EDS (Energy dispersive spectroscopy), XRD (X-rays diffraction), Scanning and Transmission Electron Microscopy (SEM) and (TEM) respectively, UV and Visible Spectroscopy and the Four Points method to study electric surface properties. Abrupt variations in electrical resistivity as the films were heated around 255 °C suggest a change of phase from semiconductor to a metallic material. The β-V₂O₅ films present electrochromic behavior under an external voltage, but Cyclic Voltammetry experiments reveal poor durability of electrochromic properties.

Key words: Vanadium oxide, oxygen content, thin films.

1. Introduction

Vanadium oxide is a material that shows a phase transition of semiconductor to metal when is heated around of a critical temperature. For the V₂O₅ compound, this phase transition occur at 257 ± 5 °C. The study of vanadium compounds in thin film configuration, has received special attention in recent times because of their interesting electrochromic and thermochromic properties and potential uses as thermal sensing, optical switches, optoelectronic devices and energy saving devices with emphasis in the development of smart windows [1]. V₂O₅ thin films have been prepared by various methods such as sputtering [2, 3], vacuum evaporation [4, 5], sol-gel [6], pulsed laser deposition [7], chemical vapor deposition[8], electron beam evaporation [9], thermal evaporation [10] and spraypyrolysis [11, 12]. They have been processed in thin film configuration to develop electrical and optical devices; especially the vanadium pentaoxide (V₂O₅), a wide band gap and n-type semiconductor material, which is widely

investigated because of its interesting thermochromic [13, 14] and electrochromic properties [15, 16].

2. Experimental

Vanadium pentaoxide (V₂O₅) thin films were deposited by RF magnetron sputtering with two deposition conditions: with and without O₂, using a V₂O₅ target. The thin films deposition was carried out using a 5 cm diameter and 3 mm thick target 99.95% pure vanadium pentoxide target (Goodfellow). The substrates were placed 50 mm in front of the magnetron and not heating was applied during the deposition. Sputtering deposition was carried out with a power of 100 W for 15 min, in a controlled Ar/O₂ atmosphere with an oxygen concentration of 10% at room temperature. The base pressure in the chamber was 10⁻⁶ torr and the working pressure was 10⁻³ torr. The V₂O₅ thin films were deposited simultaneously on corning glass substrates with and without conductive layer of fluorine doped tin oxide (SnO₂:F or FTO), with a sheet resistance of 7 ohm/sq. The V₂O₅ films' thickness was determined with an optical profilometer and from cross section SEM (Scanning electron microscopy) micrographs. The pristine vanadium

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pentoxide films present a yellow uniform color similar to those prepared by other techniques [17].

In order to measure the optical and electrical properties of as-deposited films, different bits of the same sample were heated in an oven under the same conditions, that is, at the same heating rate and at atmospheric pressure. The temperatures reached by the oven were 100, 200, 300, 400 and 500 °C respectively. The electrical performance of just mentioned samples was determined by means of the Jandel Multi Height Microposition probe equipment, using the four-points method. The XRD characterization was carried out using a Bruker D-8 Advance diffractometer with the Bragg-Brentano θ - θ geometry and CuK α radiation. The diffraction intensity as a function of the angle 2θ was measured between 8° and 90°, with steps of 0.030° and a measurement time of 35.2 s per point. The Scanning Electron Microscopy observations were performed in a LV JEOL SEM 5600 microscope and Conventional and High Resolution Electron Microscopy (CTEM and HREM respectively) were performed in a JEOL

FEG STEM 2010 microscope. Compositional characteristics were obtained in an EDS NORAN equipment in the scanning electron microscope.

3. Results

3.1 Structural Characterization

The XRD pattern displayed in Fig. 1, comes from a film prepared with a 10% O₂ concentration and deposited at RT, present diffraction peaks reported in card number 00-045-1074 (I) from the JCP2.2CA data base. The compound is identified as the β -V₂O₅ phase with tetragonal structure and lattice parameters $a = 14.259$ Å, $b = 14.259$ Å and $c = 12.576$ Å. Low intensity diffraction peaks, not presented in this work, that might correspond to a VO₂, were observed in some other XRD (X-rays diffraction) patterns of our samples.

The thickness of films reported in this work were determined by Optical Profilometry and cross section SEM micrographs measurements; It was found an average thickness of 380 nm for FTO and 440 nm for V₂O₅ films respectively.

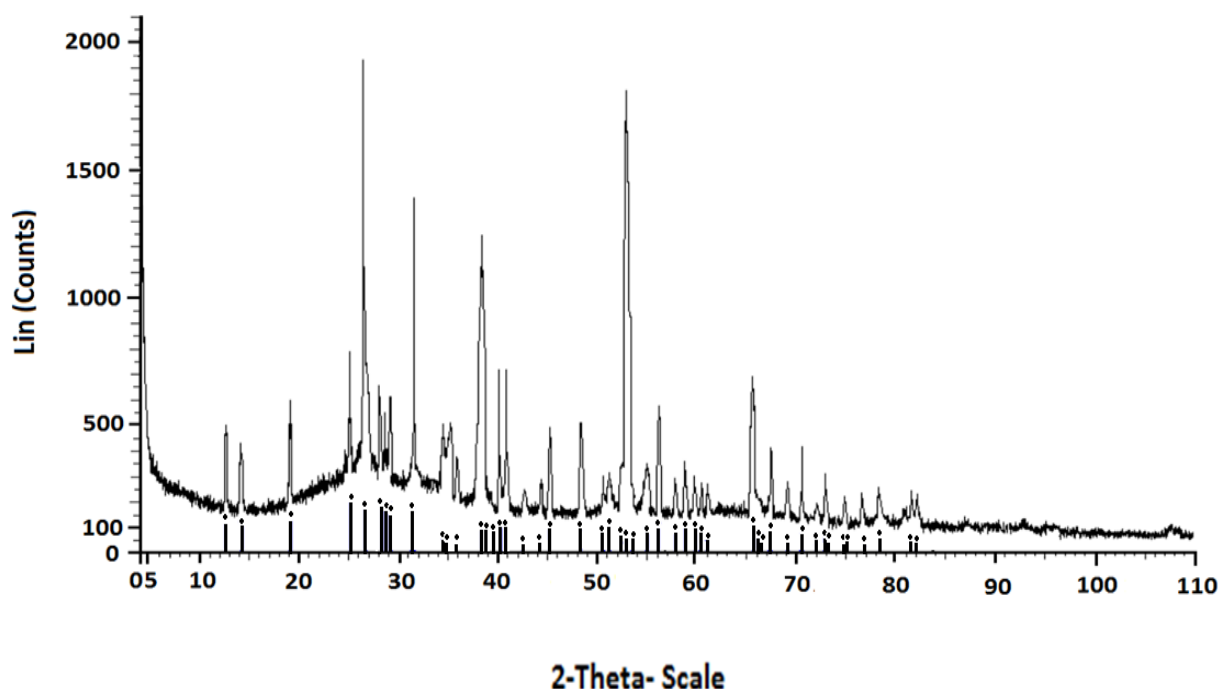


Fig. 1 A XRD pattern from a V₂O₅/FTO film deposited at room temperature. The peaks marked with blue short lines correspond to the β -V₂O₅ reflections reported in card number 00-045-1074 (I) from the JCP2.2CA data base.

3.2 Composition

The compositional properties of pristine V₂O₅ films; were studied by EDS (Energy dispersive spectroscopy) in a scanning electron microscope. In Fig. 2a, a typical EDS spectrum of a pristine sample is presented together with compositional results displayed in inserted Table I. In Fig. 2b an EDS spectra of a V₂O₅ sample, similar to the one presented in Fig. 2a, but after 60 cycles of cyclic voltammetry is displayed together with the corresponding results displayed in Table II. A comparison from quantification presented tables I and II respectively, let to detect a noticeable diminishing vanadium content in the pristine V₂O₅ samples. XPS

compositional results are displayed in Fig. 3, it can be noticed the presence of signals corresponding to VO₂ and V₂O₅ compounds in both the films synthesized with and without O₂ in the deposition chamber.

3.3 Electron Microscopy

From the bright field TEM micrograph displayed in Fig. 3a, it can be appreciated laminates of vanadium oxide film growth on a FTO substrate. Fig. 3b is a HREM micrograph, where typical configuration of our films, can be appreciated: a polycrystalline nature of vanadium oxide grains together with amorphous zones. The structural surface details of V₂O₅ films can be appreciated in SEM micrographs presented in Fig. 5.

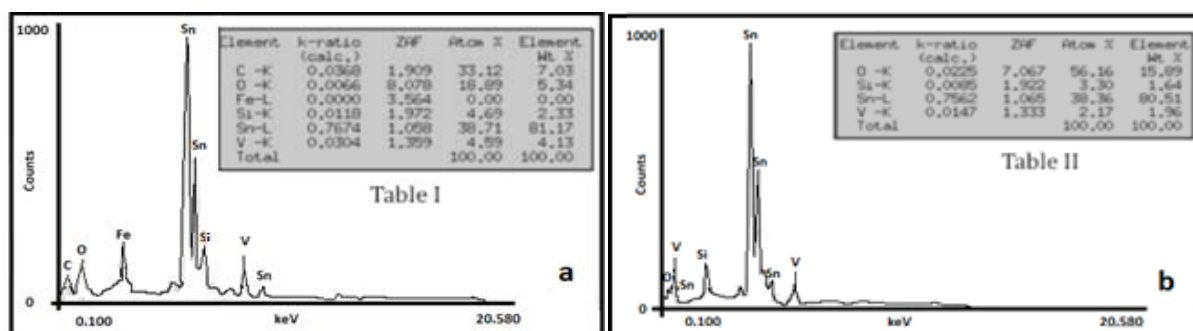


Fig. 2 A comparison of EDS quantification in tables I and II from samples before and after cyclic voltammetry experiments reveals a lot of vanadium atoms during the electrochemical process, which in turn is related to lots of electrochromic activity in V₂O₅ films.

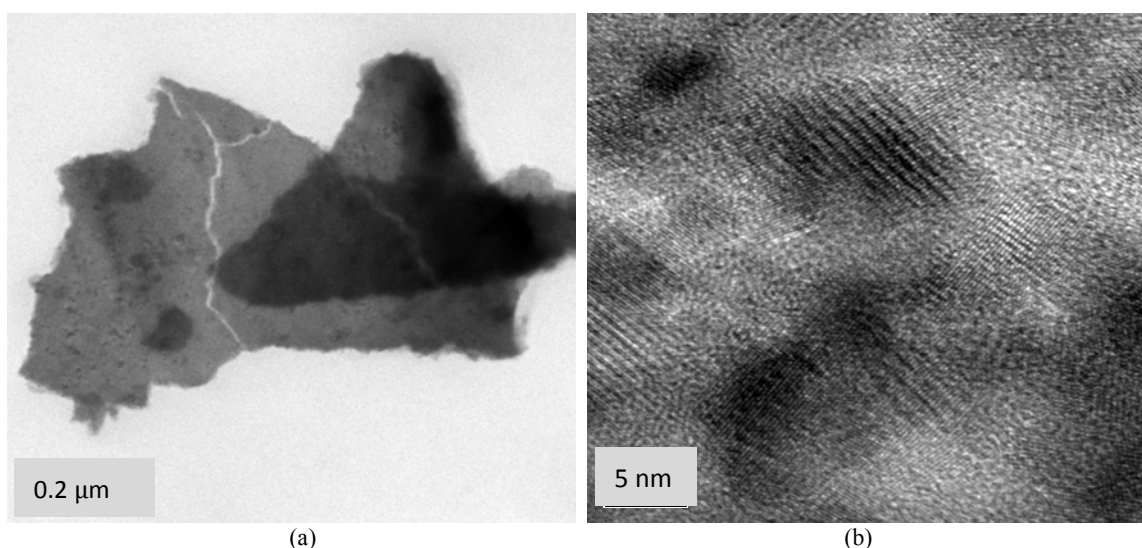


Fig. 3 (a) A bright field TEM micrograph of a pristine micro- V₂O₅/FTO film. The visible cracks were produced when the sample was stripped out from FTO/glass substrate. (b) A HREM micrograph typical from thin borders appreciated. Amorphous zones between V₂O₅/FTO grains were detected along the whole sample.

In Fig. 5a, from a sample deposited without O₂, the surface looks regular dense and compact without inter granular spaces. In Fig. 5b a micrograph from a sample deposited with an O₂ atmosphere is presented; the surface looks similar but an increase on V₂O₅ grains size can be easily recognized .

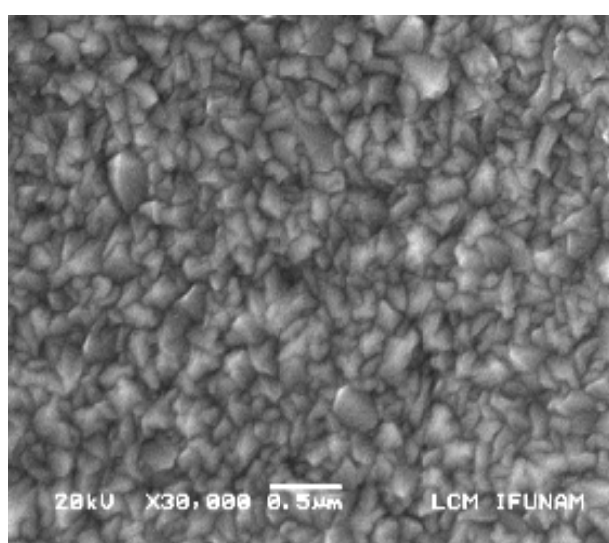
SEM micrographs presented in Fig. 4 correspond to films deposited at room temperature before and after cyclic voltammetry experiments. In Fig. 4b, modifications in grains configuration –eroded borders- and new surface details like the cracks and loss of nano

grains faceting can be observed along the sample: these changes, are related to mechanical degradation and loss of electrochromic activity as a consequence of mass and charge transport during the electrochemical experiment.

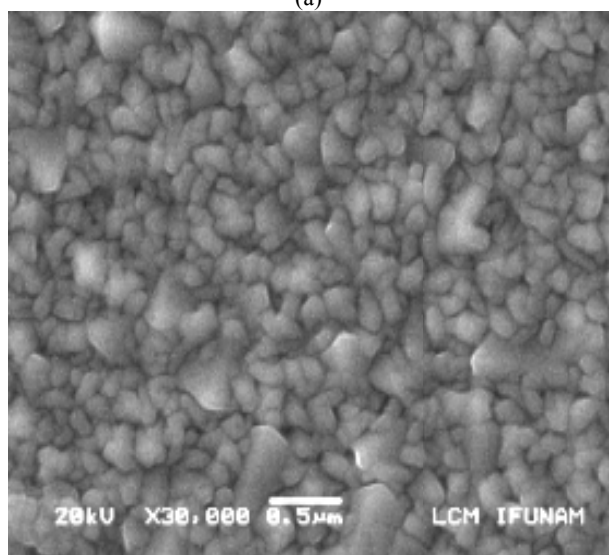
3.4 Optical Properties

Figs. 6a and 6b compares the optical transmittance for samples deposited without and with O₂ on glass and on FTO/Glass substrates respectively.

In Fig. 6a, the V₂O₅/Glass sample shows for all the

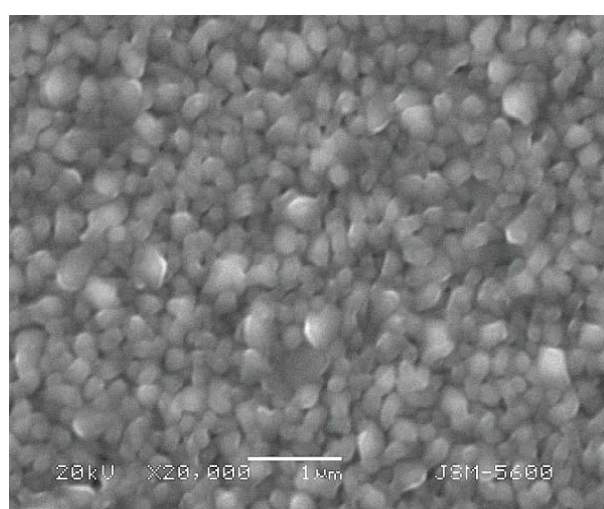


(a)

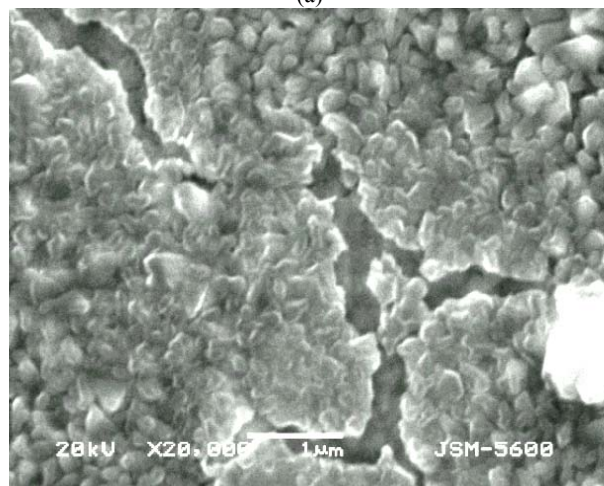


(b)

Fig. 4 SEM micrograph of a pristine V₂O₅ films produced (a) without an O₂ flux indeposition chamber, (b) with an O₂ flux in deposition chamber.



(a)



(b)

Fig. 5 (a) A SEM micrograph from a pristine V₂O₅/FTO film deposited in a O₂ atmosphere . The film looks regular and compact without inter grain spaces. (b) A SEM micrograph from a V₂O₅/FTO film after 60 cyclic voltammetry runs. Eroded grain borders and micro-cracks can be observed along the surface.

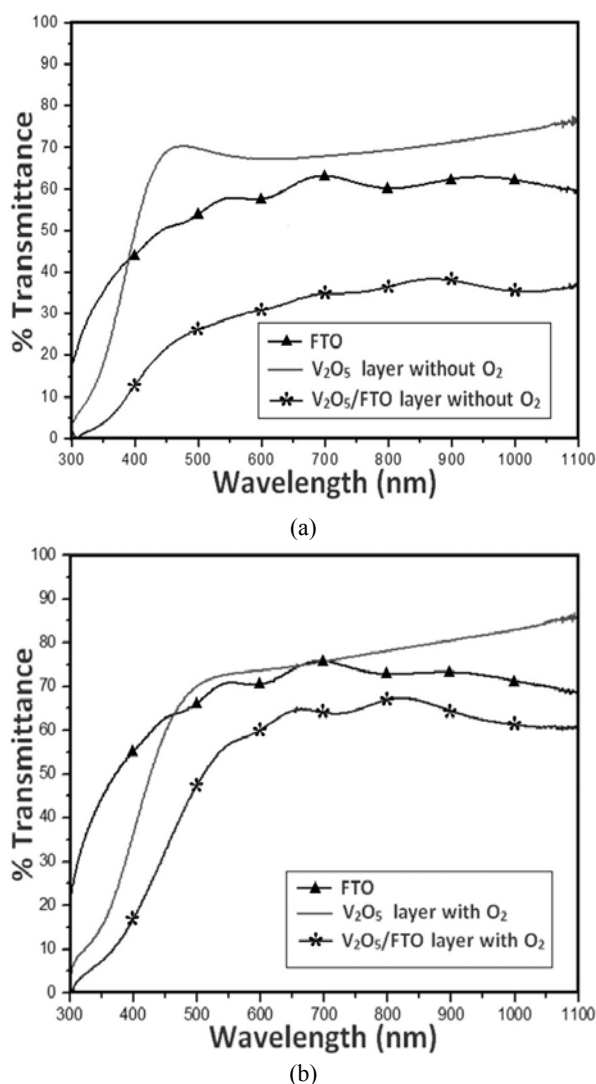


Fig. 6 (a) Optical transmittance spectra from V₂O₅ samples deposited on glass and on FTO/Glass respectively without O₂ (b) Optical transmittance spectra from FTO/Glass and V₂O₅ samples prepared on glass and on FTO/Glass respectively with O₂.

wavelengths considered, a higher transmittance than the ones observed for V₂O₅/FTO samples. In Fig. 6b, the V₂O₅ samples deposited on glass show a higher transmittance than those deposited on FTO/Glass, but with reference to graphics presented in Fig. 6a, the last samples present higher transmittance values for all the wavelengths considered. The deposited V₂O₅/FTO films display a reduced transmittance because of their thickness, but coating transmittance shows the same wavelength dependence.

3.5 Electrical Properties

The electrical properties of V₂O₅/FTO films under systematic heating were studied in order to detect variations on physical properties, during process. The electrical resistivity of pristine films deposited at RT and of those heated from 100 to 500 °C in 100 °C step were obtained with the Four Point method. In Fig. 7 the behavior of samples deposited without and with O₂ is displayed. Noticeable changes in samples electrical resistivity with temperature, were observed: The resistivity grows linearly up to 200 °C, then a sharp decrease up to close to 255 °C is observed; after a soft increase up to 300 °C; , the resistivity, again grows abruptly up to a 500 °C. The change of resistivity around the 255 °C is related with the change of a semiconductor to metallic phase [18].

3.6 Electrochromic Behavior

The electrochromic properties of our V₂O₅ films were studied in an electrochemical cell with a three electrodes configuration using the CV (Cyclic voltammetry) method. The CV experiments were performed in a potential range running from E₀ = -2,800 mV to E₁ = 2,800 mV, using platinum wire as reference electrode with a scanning rate of 1,000 mV/s. Cycling runs, were performed from 1 to 60 cycles respectively and the coloration and bleaching processes at different scanning rates, were observed for all the cases. In Fig. 8 the CV curves for 1, 10, 30 and 60 cycles are presented; it can be observed that cathodic and anodic peaks decrease progressively as the cycle numbers is increased. From SEM micrographs of films deposited at room temperature and after cyclic voltammetry experiments, like the one presented in Fig. 6b, it were detected modifications in grains configuration and surface details that are related with sample degradation and loss of electrochromic activity as a consequence of mass and charge transport and transference during the experiment.

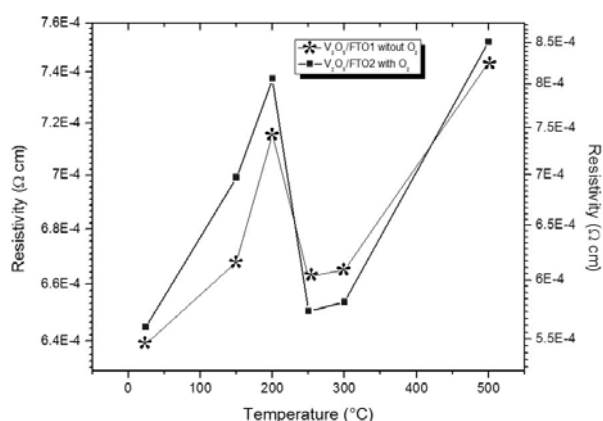


Fig. 7 Resistivity versus temperature graphics for samples deposited with O₂ and without O₂. Similar behavior is observed for both samples showing an abrupt change in resistivity values around 255 °C which is associated to a semiconductor-metal transition.

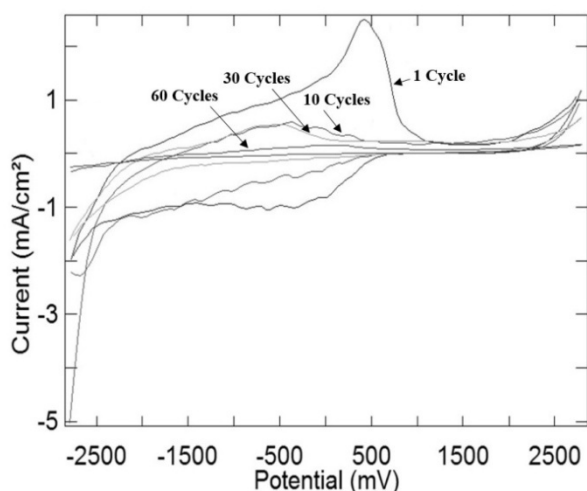


Fig. 8 Cyclic Voltammetry graphics from a V₂O₅/FTO sample deposited in an O₂ atmosphere.

4. Conclusions

V₂O₅ in thin films configurations were produced by MS in vacuum and in an O₂ atmosphere on glass and on FTO substrates. From XRD patterns results the beta-V₂O₅ phase was identified. From SEM micrographs it is observed that grains with higher size appears in samples grown in an O₂ atmosphere and it is expected to be related with changes observed in optical transmittance and electrical conductivity parameters. An abrupt change in electrical resistivity was observed when V₂O₅ samples were heated around 255 °C and this variation is related with a

metal-semiconductor transition. The samples present electrochromic properties, but these disappears after a low number of voltammetric cycles; this behavior is related to structural instability as a consequence of intense mass and charge transport phenomena

Acknowledgements

The financial support of DGAPA-UNAM Project IN 105514 is appreciated and recognized. Also we thank the financial support of DGAPA-UNAM to the Posdoctoral Position of Dr. Francisco Hernández in our laboratory and recognize the technical assistance of Diego Quiterio and Roberto Hernández in electron microscopy works.

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